## Features

- Selected to specific on-line intensity and radiant intensity ranges.
- Low cost plastic end looking package.
- Mechanically and spectrally matched to the LTR-4206 series of phototransistor.
- The LTE-4206 series are made with Gallium Aluminum Arsenide window layer on Gallium Arsenide infrared emitting diodes.


## Description

The LTE-4206 series are high intensity Gallium Aluminum Arsenide infrared emitting diodes mounted in clear plastic end looking packages. The LTE-4206 series provides a broad range of intensity selection. Suffix C-smoke color lens.

## Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25 \mathrm{~mm}\left(.010^{\prime \prime}\right)$ unless otherwise noted.
3. Protruded resin under flange is 1.5 mm (.059") max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specifications are subject to change without notice.

## Absolute Maximum Ratings at $\mathrm{Ta}=25^{\circ} \mathrm{C}$

| Parameter | Maximum Rating | Unit |
| :--- | :---: | :---: |
| Power Dissipation | 90 | mW |
| Peak forward Current (300pps, $10 \mu$ s pulse) | 1 | A |
| Continuous Forward Current | 60 | mA |
| Reverse Voltage | 5 | V |
| Operating Temperature Range | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |
| Storage Temperature Range | $-55^{\circ} \mathrm{C}$ to $+100^{\circ} \mathrm{C}$ |  |
| Lead Soldering Temperature <br> $[1.6 m m ~(.063$ in.) from body $]$ | $260^{\circ} \mathrm{C}$ for 5 Seconds |  |

## Electrical Optical Characteristics at $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test <br> Condition |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| *Aperture Radiant Incidence | Ee | 0.3 | 0.7 |  | $\mathrm{~mW} / \mathrm{cm}^{2}$ | $\mathrm{I}_{\mathrm{F}=20 \mathrm{~mA}}$ |
| Radiant Intensity | le | 2.25 | 5.26 |  | $\mathrm{~mW} / \mathrm{sr}$ | $\mathrm{I}_{\mathrm{F}=2}=20 \mathrm{~mA}$ |
| Peak Emission Wavelength | $\lambda$ Peak |  | 940 |  | nm | $\mathrm{I}_{\mathrm{F}=2}=20 \mathrm{~mA}$ |
| Spectral Line Half-Width | $\Delta \lambda$ |  | 50 |  | nm | $\mathrm{I}_{\mathrm{F}=20 \mathrm{~mA}}$ |
| Forward Voltage | VF |  | 1.2 | 1.6 | V | $\mathrm{IF}_{\mathrm{F}=20 \mathrm{~mA}}$ |
| Reverse Current | IR |  |  | 100 | $\mu \mathrm{~A}$ | $\mathrm{~V}_{\mathrm{R}=5 \mathrm{~V}}$ |
| View Angle (See Fig.6) | $2 \theta 1 / 2$ |  | 20 |  | deg |  |

Note: *Ee is a measurement of the average radiant incidence upon a sensing area $1 \mathrm{~cm}^{2}$ in perpendicular to and

## Typical Electrical/Optical Characteristic Curves ( $25^{\circ} \mathrm{C}$ Ambient Temperature Unless Otherwise Noted)



FIG. 1 SPECTRAL DISTRIBUTION


FIG. 3 FORWARD CURRENT VS. FORWARD VOLTAGE


FIG. 5 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT


FIG. 2 FORWARD CURRENT VS. AMBIENT TEMPERATURE


FIG. 4 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE


FIG. 6 RADIATION DIAGRAM

